



First Named Inventor	Michael Smith
Serial No.	10/656,636
Filing Date	September 5, 2003
Group Art Unit	2811
Examiner Name	Unknown
Confirmation No.	8125
Attorney Docket No.	400.245US01
Title: TRENCH CORNER EFFECT BIDIRECTIONAL FLASH MEMORY CELL	

**INFORMATION DISCLOSURE  
STATEMENT  
FORM PTO-1449**

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